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## 1 IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

2 Priority APPLICATION SERIAL NO. ..... 08/993,663  
3 Priority FILING DATE ..... December 18, 1997  
4 INVENTORSHIP ..... Salman Akram et al.  
5 ASSIGNEE ..... Micron Technology, Inc.  
6 Priority GROUP ART UNIT ..... 2812  
7 Priority EXAMINER ..... S. Mulpuri  
8 ATTORNEY'S DOCKET NO. ..... MI22-1178  
9 TITLE: Methods of Forming a Transistor Gate (As Amended)

ic518 U.S. PTO  
09/29/132 PT  
04/14/99

7 INFORMATION DISCLOSURE STATEMENT8 PURSUANT TO 37 C.F.R. §§ 1.56, 1.97 AND 1.98

9 In compliance with 37 C.F.R. §§ 1.56, 1.97 and 1.98, your attention is directed  
10 to the United States patents and other references listed on the attached Form PTO-  
11 1449. No admission is made regarding whether all the submitted references are prior  
12 art.

13 The listed references were cited by, or submitted to, the Office in the parent,  
14 co-pending application of the above-identified application. The above-identified  
15 application is a continuation application of co-pending application Serial No.  
16 08/993,663, filed December 18, 1997. Such prior disclosure is sufficient for the  
17 above-identified application as far as copies of the references are concerned. 37  
18 C.F.R. § 1.98(d) and MPEP § 609(2).

19  
20 Respectfully submitted,

21 Dated: April 14, 1999

22 Attorney:

James D. Shaurette  
Reg. No.: 39,833

